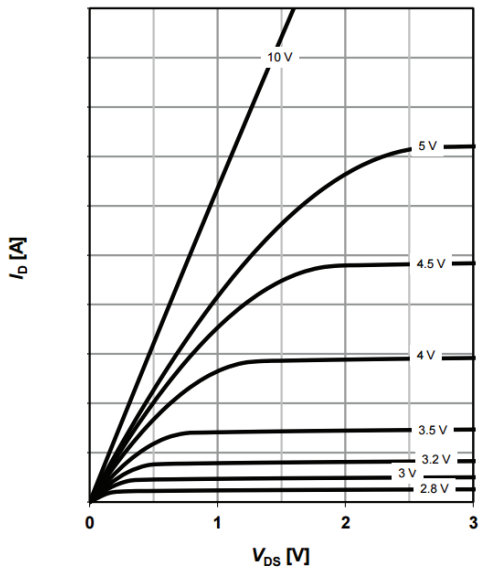
MOSFET Switching Behaviors

5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

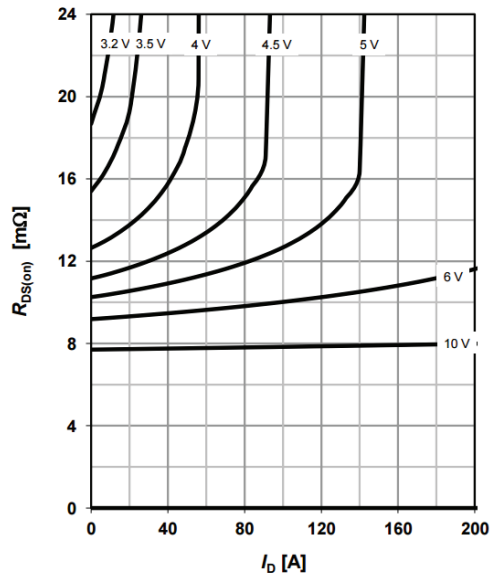
parameter: V_{GS}



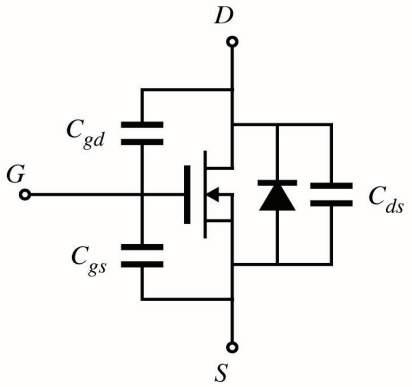
6 Typ. drain-source on resistance

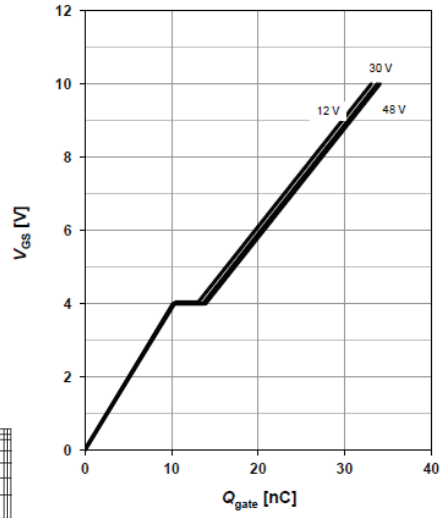
$R_{DS(on)}$=f(I_D); T_j=25 °C

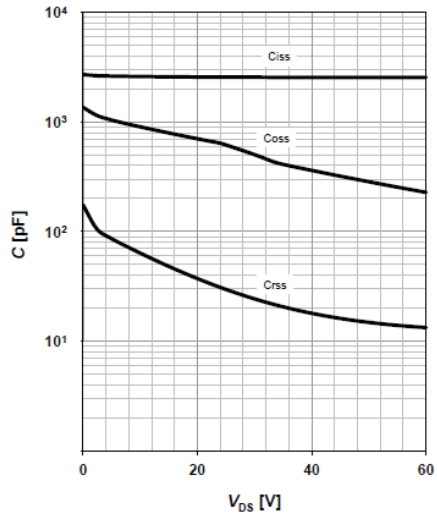
parameter: V_{GS}

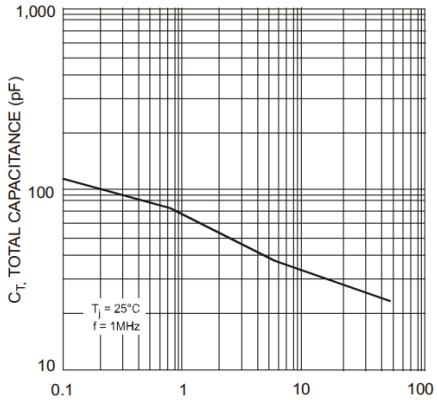


MOSFET Stored Charge

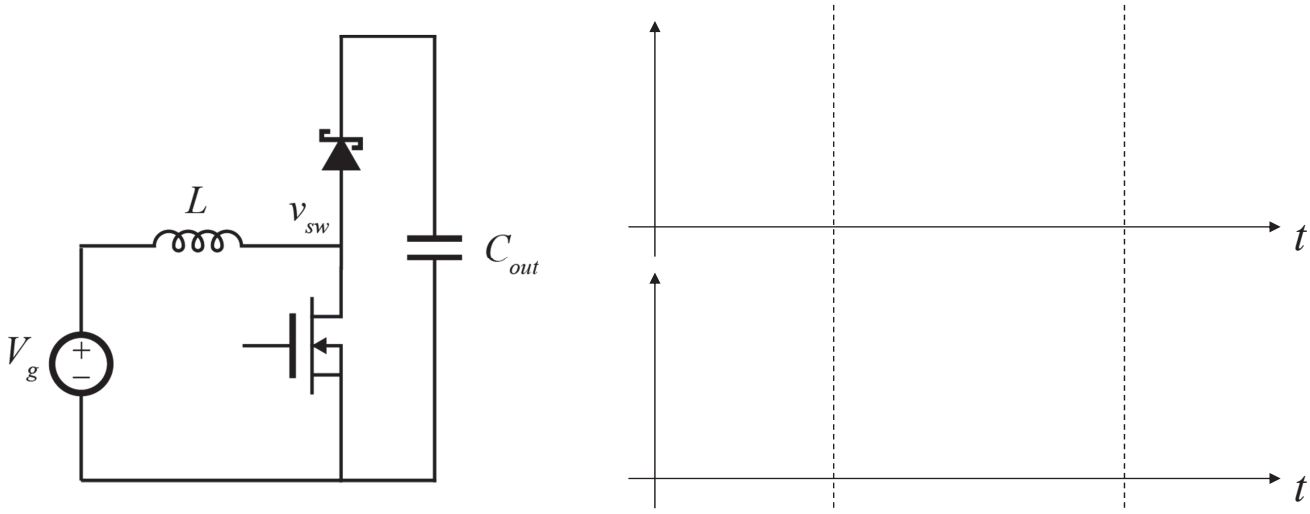




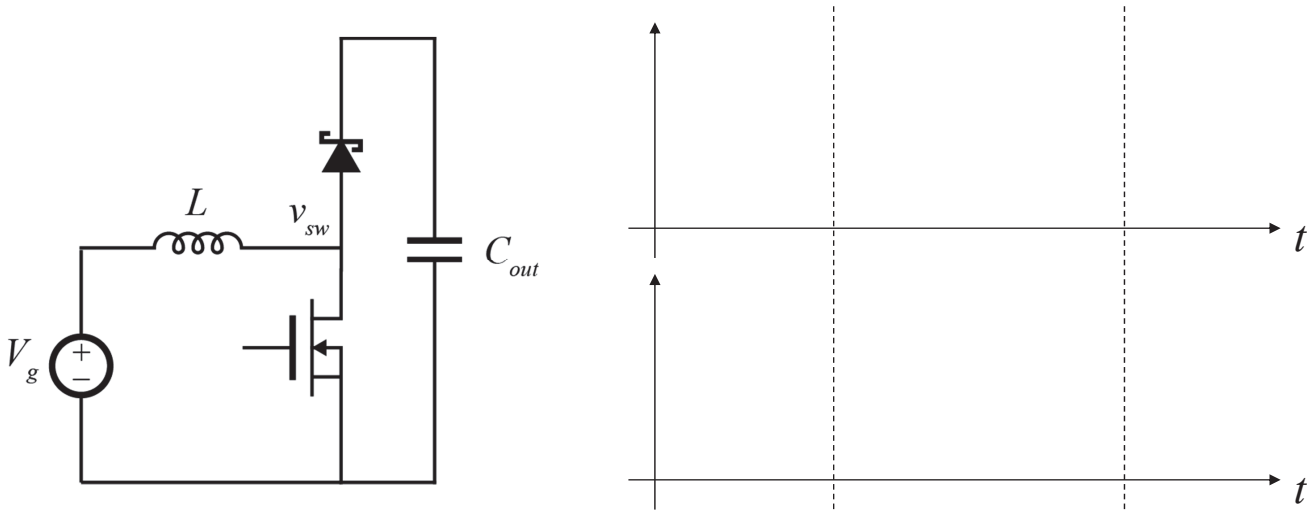




Device Capacitances



Device Capacitances



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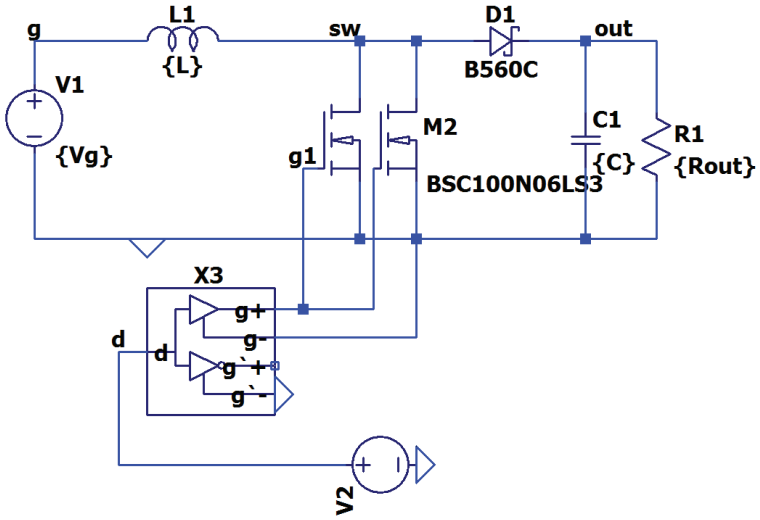
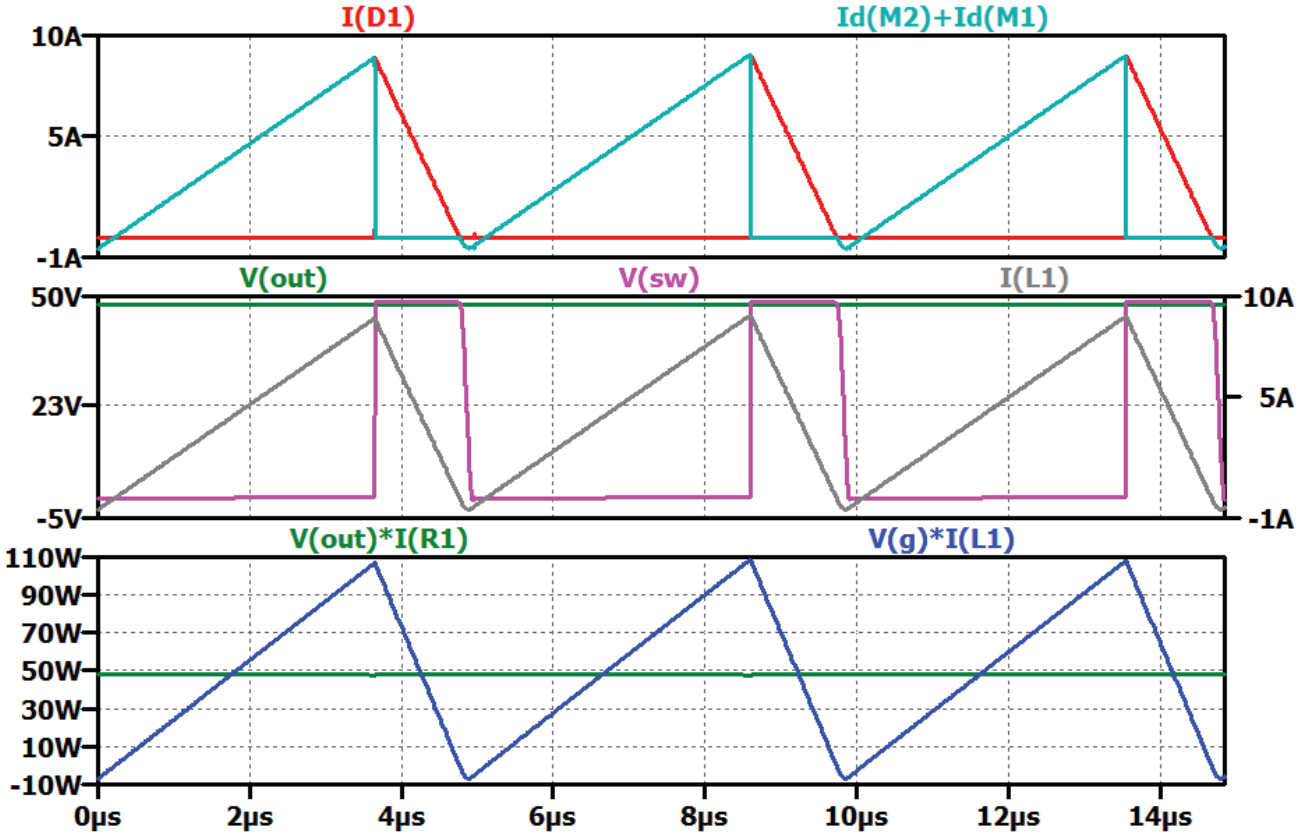
DCM: Soft Switching

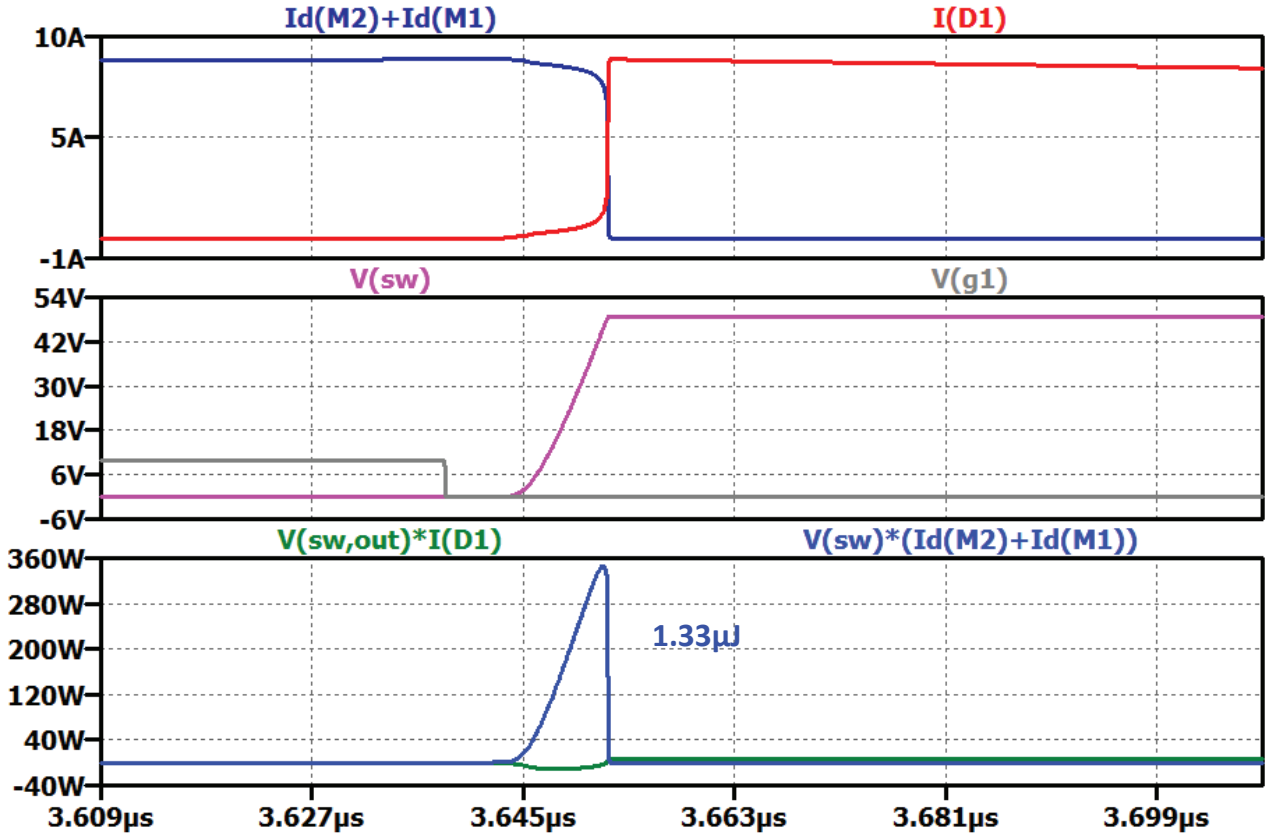


L	C_{out}	f_s	Diode	η (Sim)
22uH	22uF	202k	Si (FR)	93.9%
22uH	22uF	202k	Si Schottky	95.8%
4.6uH	22uF	202k	Si Schottky	98.2%

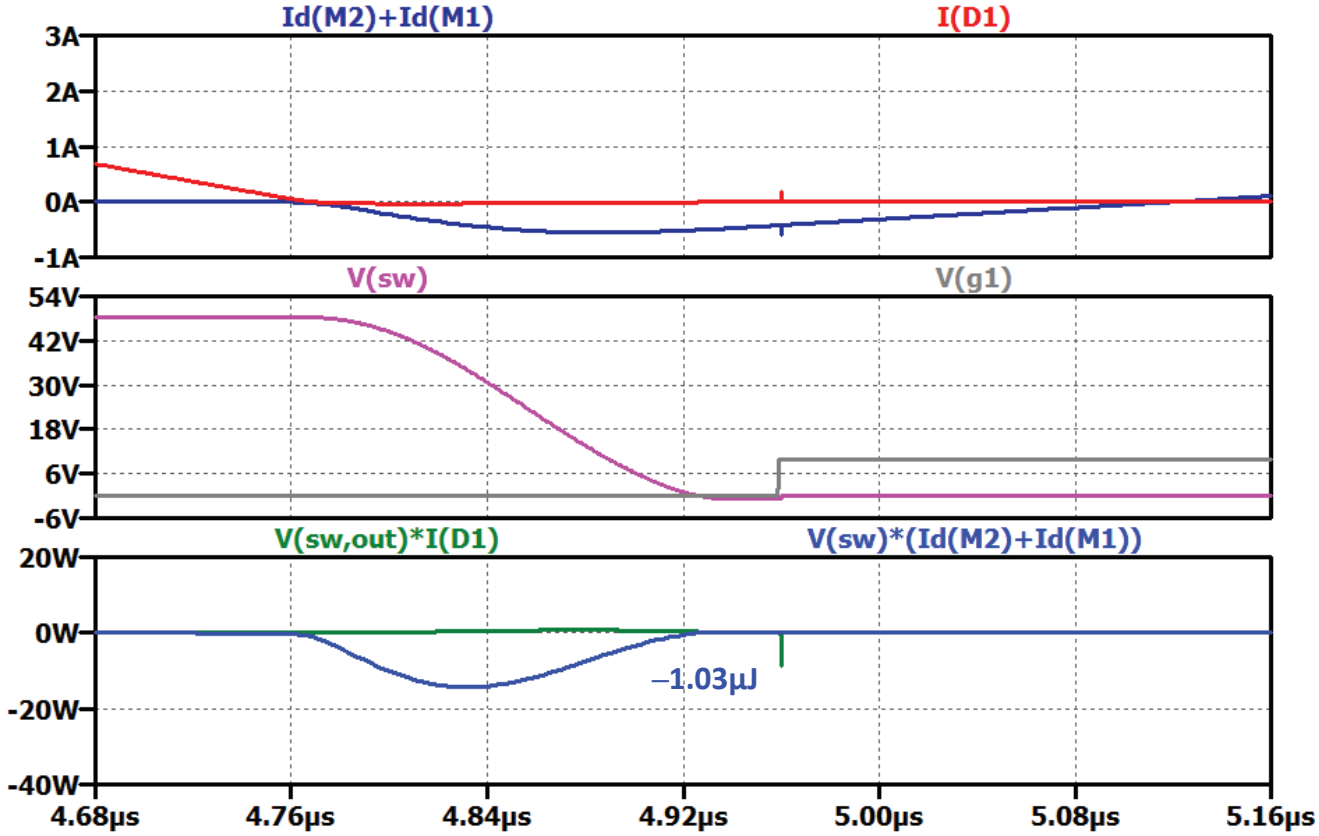
DCM Simulation



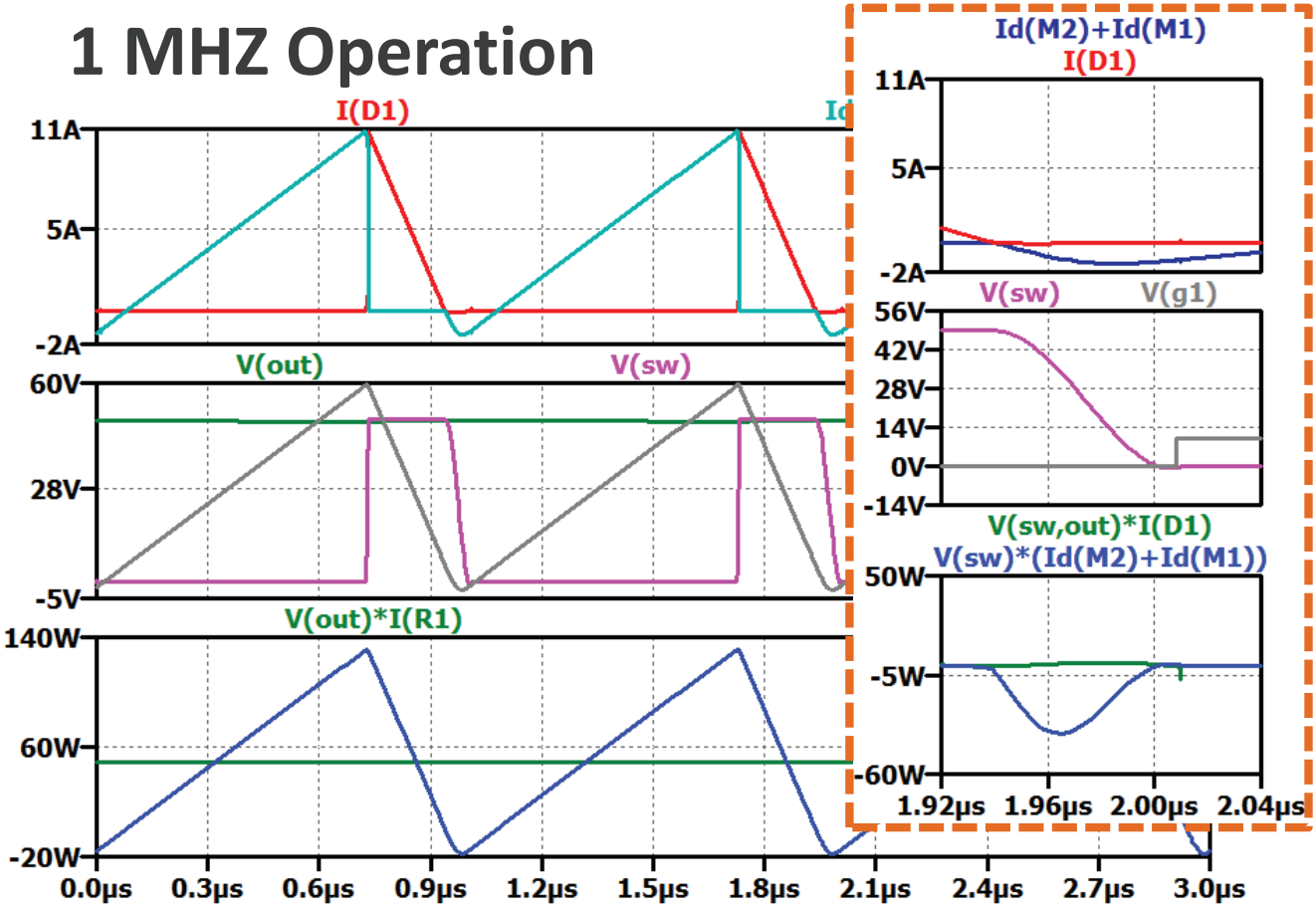
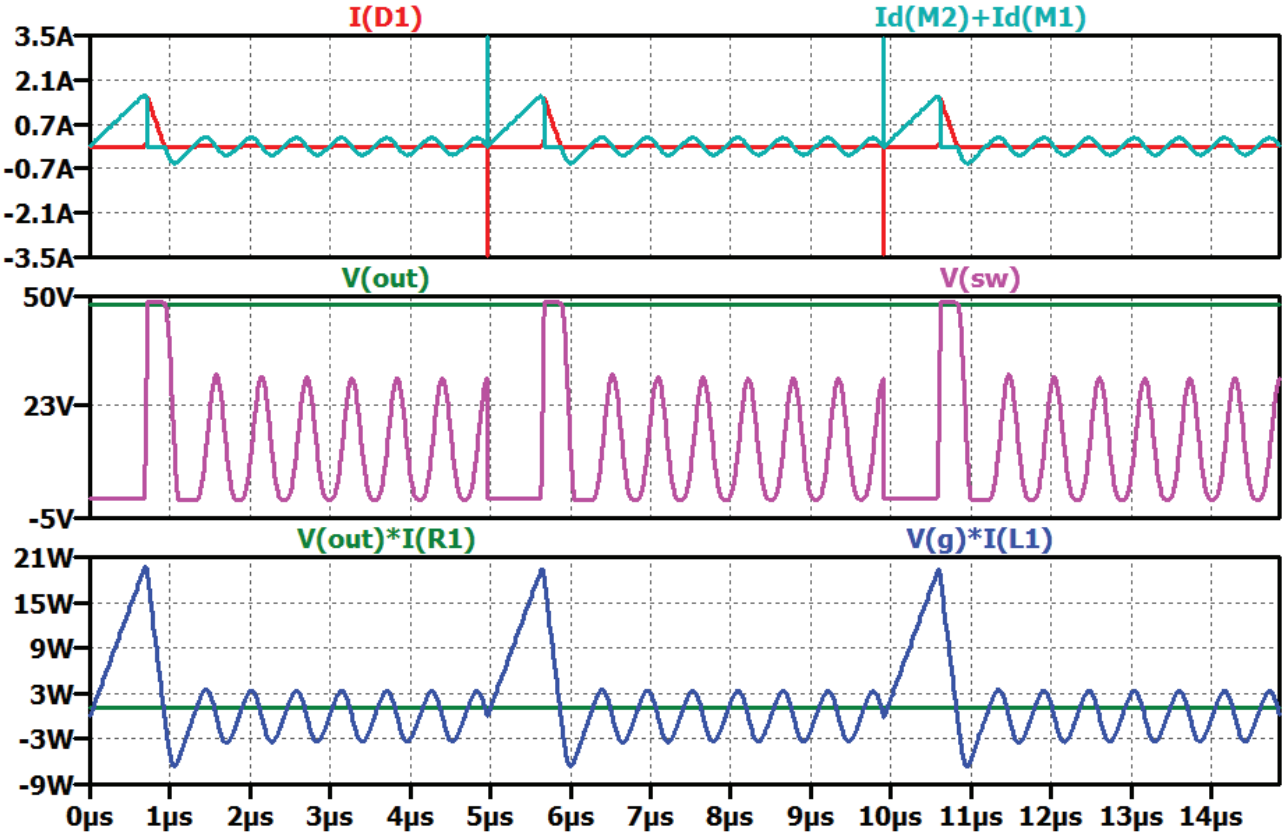
MOSFET Turn-Off



MOSFET Turn-On



1 MHZ Operation



Low Power Operation